

REMARKS

Claims 7-13 are pending. Claim 7 has been amended. Claim 13 is newly presented. Reconsideration and allowance of the present application based on the following remarks are respectfully requested.

Claim Rejections Under 35 U.S.C. § 102 and 103

Claims 7, 8, and 10 were rejected under 35 U.S.C. § 102(e) over Sung et al. (U.S. Publication No. 2001/0026968) and claims 9 and 11 were rejected under 35 U.S.C. § 103(a) in view of Sung. Applicants respectfully traverse these rejections.

The present invention relates to forming a CAM (Code Address Memory) while Sung relates to a method of forming a split-gate flash cell. A structure of the CAM cell is different from that of the split-gate flash cell.

Specifically, amended claim 7 recites, in part, a method of manufacturing a code address memory cell in a peripheral circuit region and a flash memory cell in a cell region, the method that includes sequentially forming an insulating film including an oxide film and a nitride film and a second polysilicon film on the entire structure including the cell region and the peripheral circuit region, the insulating film being formed under the second polysilicon film.

In contrast, Sung discloses an oxide layer 170 and a control gate 160. The office action alleges that the oxide layer 170 is analogous to the insulating film recited in claim 7 and that the control gate 160 is analogous to the second polysilicon film recited in claim 7 (See, Office Action at page 3) As seen in Figure 2F, the control gate 160 is under the oxide layer 170. Accordingly, the structure disclosed in Sung is, at best, a polysilicon film under an insulating film and not an insulating film formed under the second polysilicon film, as recited in amended claim 7. Accordingly, Sung fails to teach or suggest a method of manufacturing a code address memory cell in a peripheral circuit region and a flash memory cell in a cell region that includes sequentially forming an insulating film including an oxide film and a nitride film and a second polysilicon film on the entire structure including the cell region and the peripheral circuit region, the insulating film being formed under the second polysilicon film, as recited in amended claim 7.

Claims 8-11 are believed allowable for at least the reasons presented above with respect to claim 7 by virtue of their dependence upon claim 7. Accordingly, Applicants respectfully request reconsideration and withdrawal of these rejections.

Allowable Subject Matter and New Claims

Applicants appreciate the Examiner's indication that claim 12 contained allowable subject matter and would be allowable if rewritten in independent form. Accordingly, Applicants have added new claim 13 which includes the subject matter of claim 12.

Additionally, in view of the foregoing, Applicants submit that all of the claims (claims 7-13) are allowable.

Conclusion

Therefore, all objections and rejections having been addressed, it is respectfully submitted that the present application is in a condition for allowance and a Notice to that effect is earnestly solicited.

Should any issues remain unresolved, the Examiner is encouraged to contact the undersigned attorney for Applicants at the telephone number indicated below in order to expeditiously resolve any remaining issues.

Respectfully submitted,

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Date: June 6, 2005